

ABSTRACT

A method for manufacturing a semiconductor device of the present invention includes at least the following three steps.

5 (A) A step of preparing a structure including a semiconductor wafer having a circuit-formed surface and an adhesive film (100) attached to the circuit-formed surface side of the semiconductor wafer

(B) A step of back grinding a surface on a side opposite to the
10 circuit-formed surface side of the semiconductor wafer

(C) A step of radiating ultraviolet rays to the adhesive film (100) and then removing the adhesive film (100) from the semiconductor wafer

As the adhesive film (100), an adhesive film including a base
15 material layer (10) and an ultraviolet-curable adhesive resin layer (20) provided on one surface side of the base material layer (10) is used. In addition, in the adhesive film (100), the adhesive resin layer (20) includes an ultraviolet-curable adhesive resin, and a saturated electrostatic potential V_1 of a surface of the adhesive
20 resin layer (20) after ultraviolet curing, which is measured using a specific method, is equal to or less than 2.0 kV.